NEC

MOS Field Effect Power Transistors

Phase-out/Discontinued

μPA1710

SWITCHING
P-CHANNEL POWER MOS FFT
INDUSTRIAL USE

DESCRIPTION

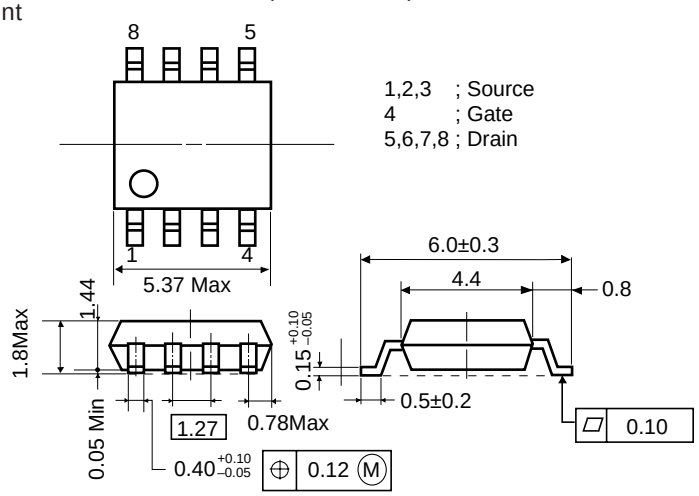
This product is P-Channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of notebook computers.

FEATURES

- Low On-Resistance
  $R_{DS(on)1}$ = 70 mΩ Max.(V_{GS} = –10V, I_D = –2.5A)
  $R_{DS(on)2}$ = 0.16 Ω Max.(V_{GS} = –4V, I_D = –2.0A)
- Low C_{iss} C_{iss} = 980pF Typ.
- Built-in G-S Protection Diode
- Small and Surface Mount Package
  (Power SOP8)

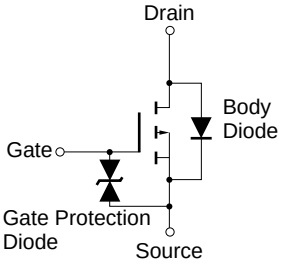
PACKAGE DIMENSIONS

(in millimeter)



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, All terminals are connected)

Drain to Source Voltage	V_{DSS}	–30	V
Gate to Source Voltage	V_{GSS}	∓ 20	V
Drain Current (DC)	$I_{D(DC)}$	∓ 5.0	A
Drain Current (pulse)*	$I_{D(pulse)}$	∓ 20	A
Total Power Dissipation (T_A = 25°C)**	P_T	2.0	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	–50 to +150	°C



* PW≤10 μs, Duty Cycle ≤ 1%

** Mounted on ceramic substrate of 1200 $mm^2 \times 0.7$ mm

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if voltage exceeding the rated voltage may be applied to this device.

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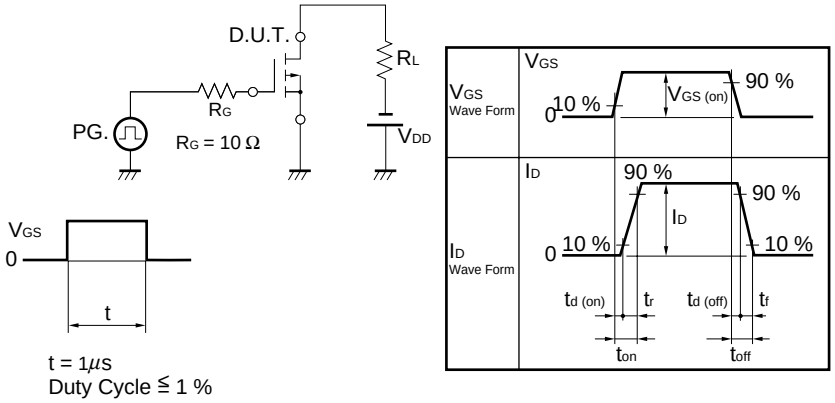
ELECTRICAL CHARACTERISTICS (T_A = 25 °C, All terminals are connected)

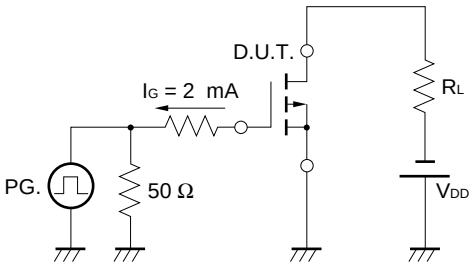
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain to Source On-state Resistance	$R_{DS(on)1}$	V_{GS} = –10V, I_D = –2.5A		50	70	mΩ
	$R_{DS(on)2}$	V_{GS} = –4V, I_D = –2.0A		110	160	mΩ
Gate to Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = –10V, I_D = –1mA	–1.0	–1.5	–2.5	V
Forward Transfer Admittance	$\|y_{fs}\|$	V_{DS} = –10V, I_D = –2.5A	3.0	5.0		S
Drain Leakage Current	I_{DSS}	V_{DS} = –30V, V_{GS} = 0			–10	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ∓20V, V_{DS} = 0			∓10	μA
Input Capacitance	C_{iss}	V_{DS} = –10V		980		pF
Output Capacitance	C_{oss}	V_{GS}=0		780		pF
Reverse Transfer Capacitance	C_{rss}	f = 1MHz		430		pF
Turn-On Delay Time	$t_{d(on)}$	ID = –2.5A		25		ns
Rise Time	t_r	$V_{GS(on)}$ = –10V		80		ns
Turn-Off Delay Time	$t_{d(off)}$	V_{DD} = –15V		100		ns
Fall Time	t_f	R_G = 10Ω		100		ns
Total Gate Charge	Q_G	I_D = –5.0A		38		nC
Gate to Source Charge	Q_{GS}	V_{DD} = –24V		3.6		nC
Gate to Drain Charge	Q_{GD}	V_{GS} = –10V		17		nC
Body Diode Forward Voltage	$V_{F(S-D)}$	I_F = 5.0A, V_{GS} = 0		0.8		V
Reverse Recovery Time	t_{rr}	I_F = 5.0A, V_{GS} = 0		85		ns
Reverse Recovery Charge	Q_{rr}	di/dt = 50A/μs		200		nC

Test Circuit 1 Switching Time

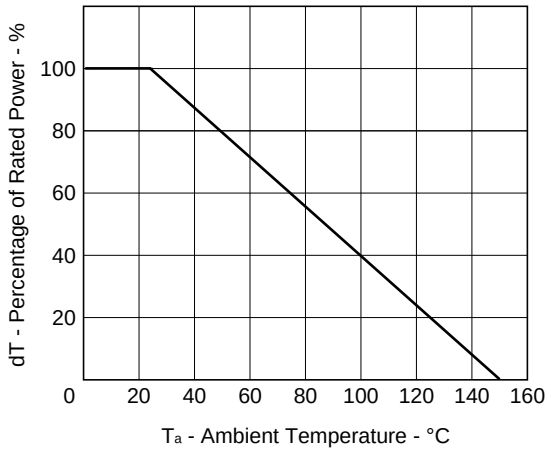


t = 1μs
Duty Cycle ≦ 1 %

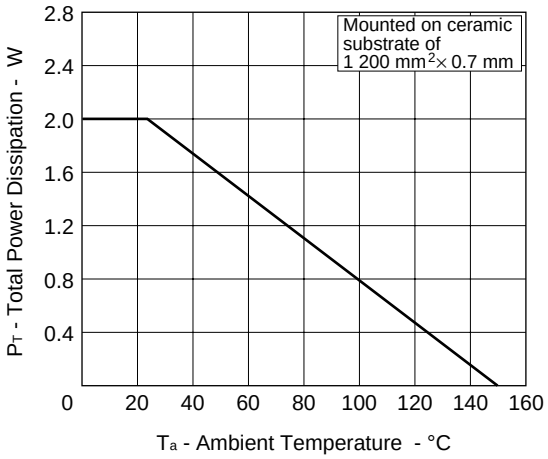
Test Circuit 2 Gate Charge



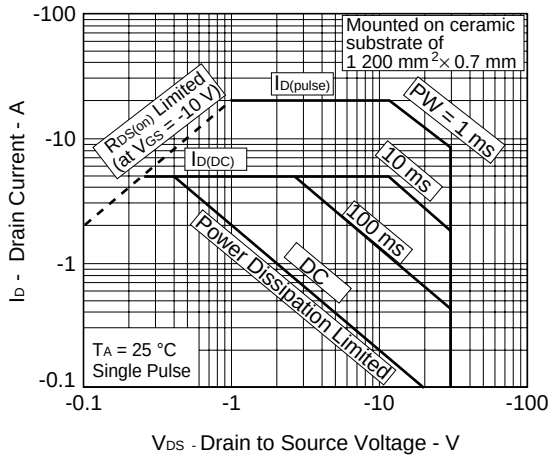
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



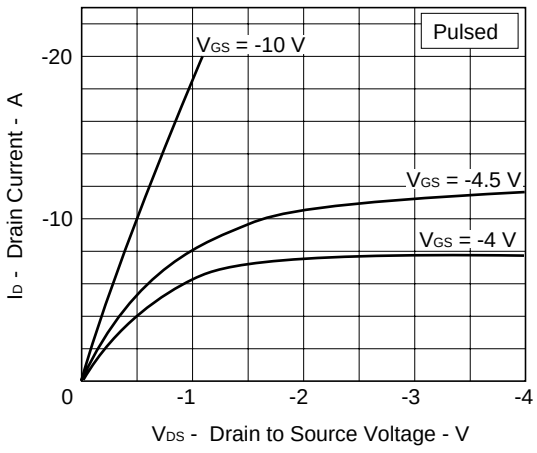
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



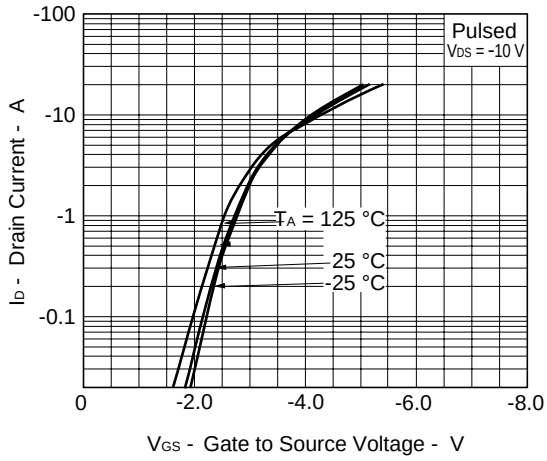
FORWARD BIAS SAFE OPERATING AREA



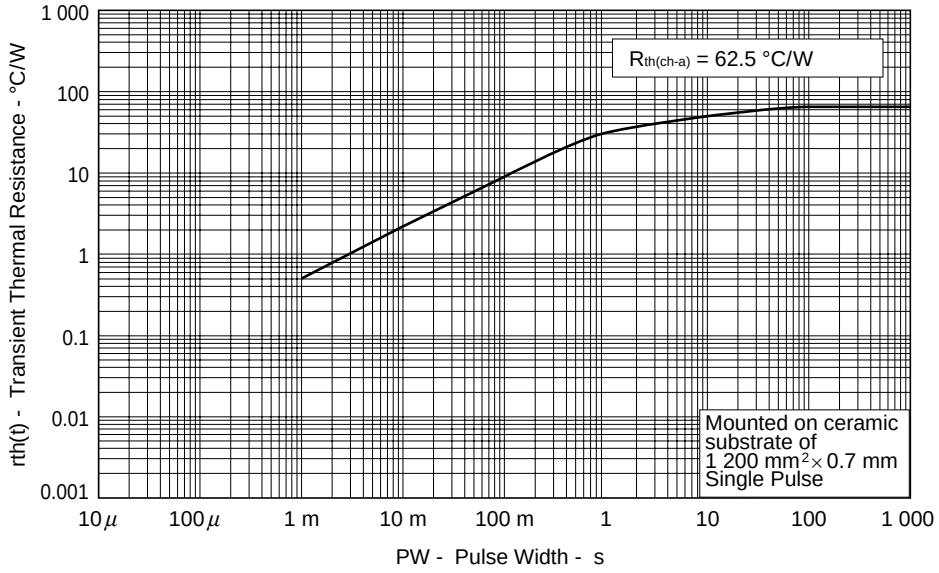
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



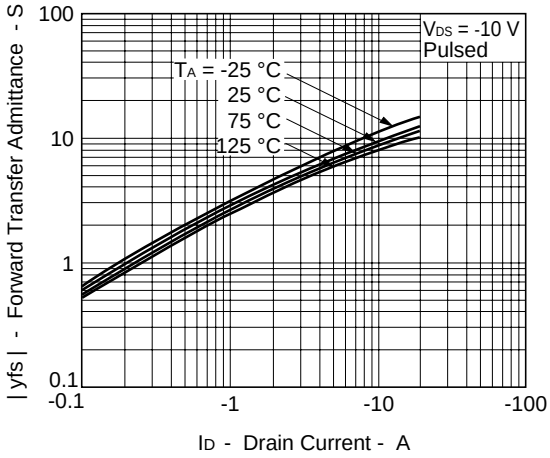
FORWARD TRANSFER CHARACTERISTICS



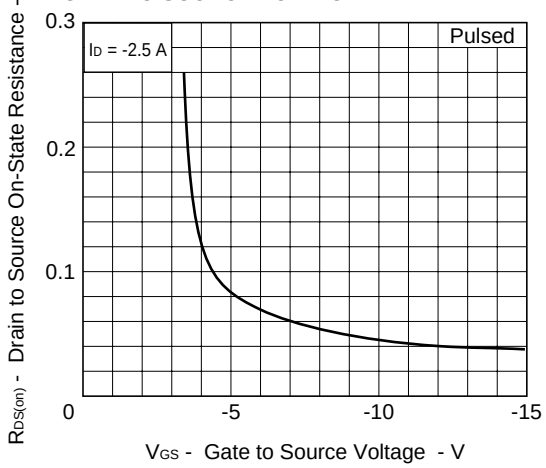
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



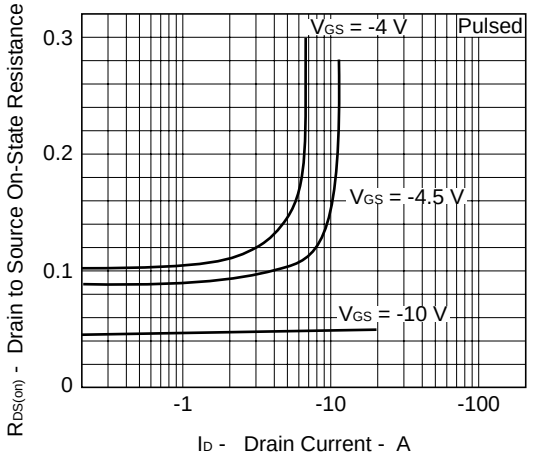
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



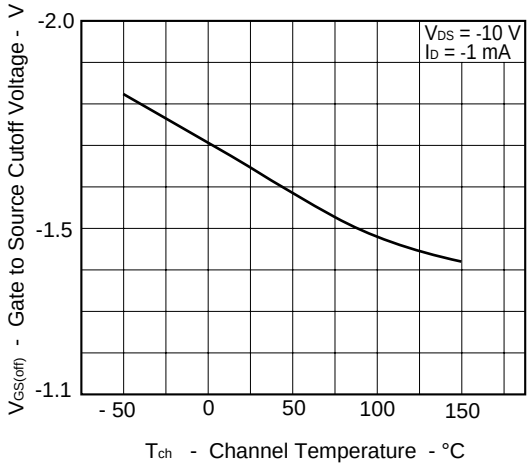
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



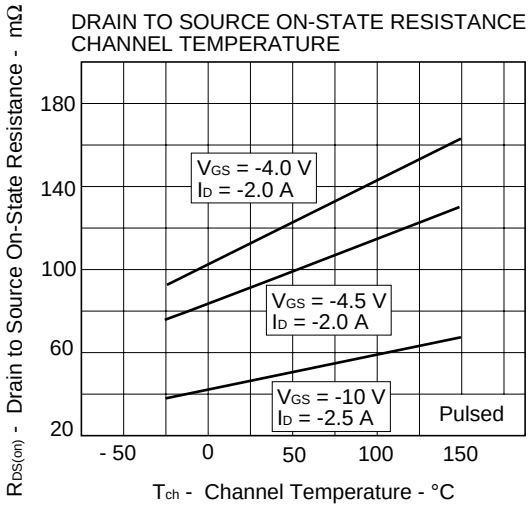
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



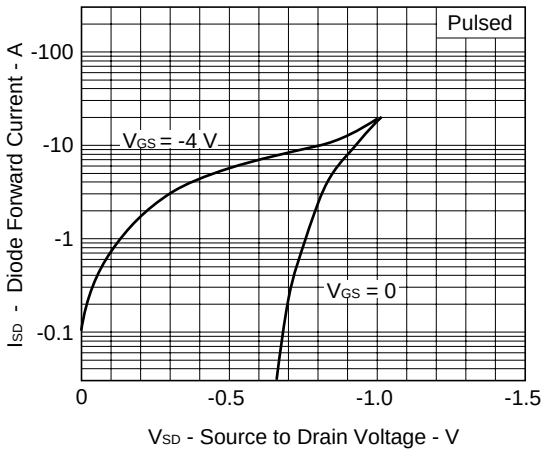
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



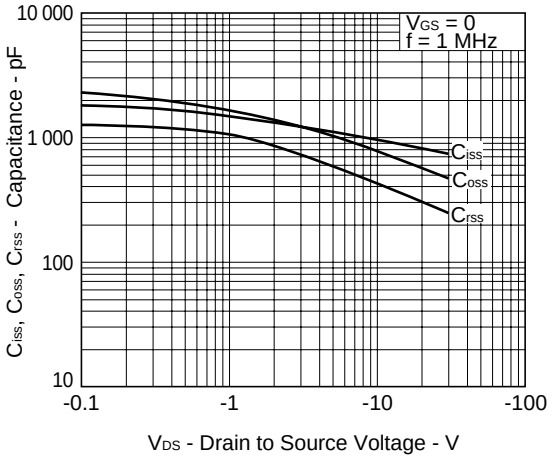
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



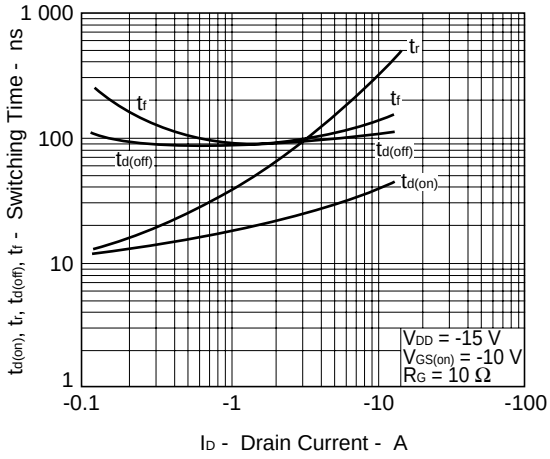
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



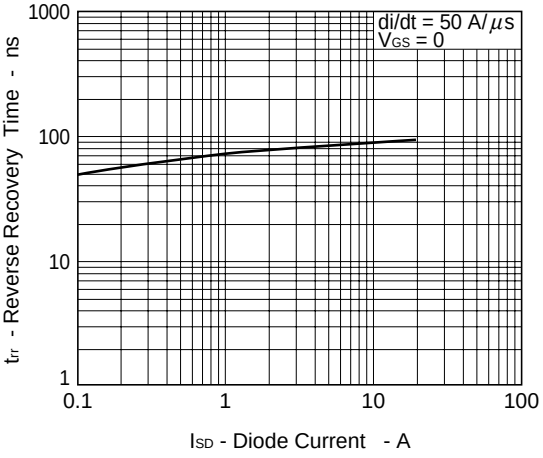
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



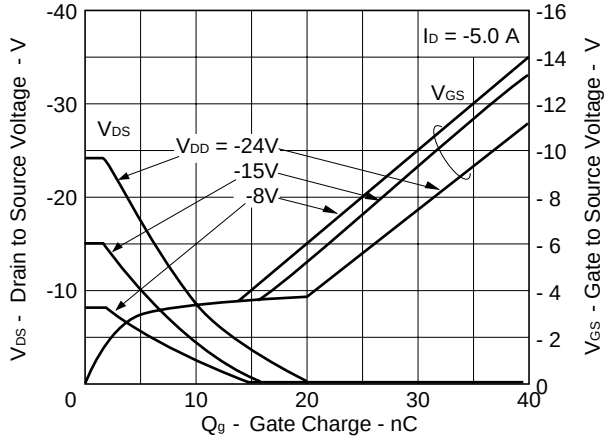
SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DRAIN CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system	TEI-1202
Quality grade on NEC semiconductor devices	IEI-1209
Semiconductor device mounting technology manual	C10535E
Semiconductor device package manual	C10943X
Guide to quality assurance for semiconductor devices	MEI-1202
Semiconductor selection guide	X10679E
Power MOS FET features and application switching power supply	TEA-1034
Application circuits using Power MOS FET	TEA-1035
Safe operating area of Power MOS FET	TEA-1037

[MEMO]

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